Ramping New Products Yields in the Deep Submicron Age

ISQED 2000 March 21st, 2000 PDF Solutions, Inc. John K. Kibarian



Major Points

- Increasing design and process complexity becoming critical factor leading to yield loss
- Systematic yield loss component is significant, growing, and recoverable
- Fundamental new approach, focused on integration between design, process and manufacturing, is required to recover yield loss



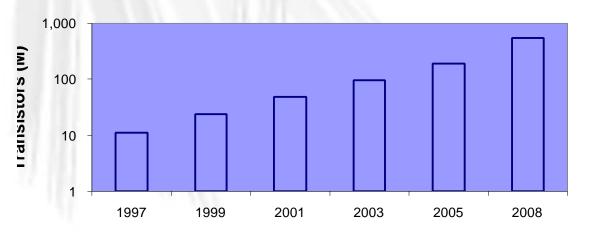
Outline

- Product Yield Ramps: the market pressures
- The Design-Manufacturing Integration Problem
- Solution
- Examples
- Concluding remarks



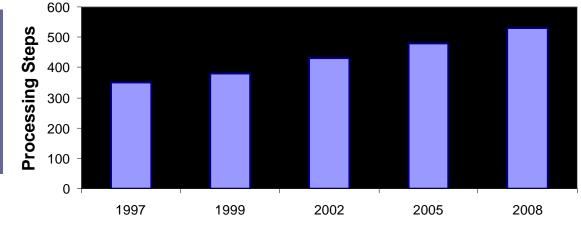
Complexity is Increasing Across the Board

IC Complexity: Transistors



IP Reuse is Critical to Get Designs to Market Faster

Unless Corrected, Increased Processing Complexity Reduces Yield up to 5% per Year



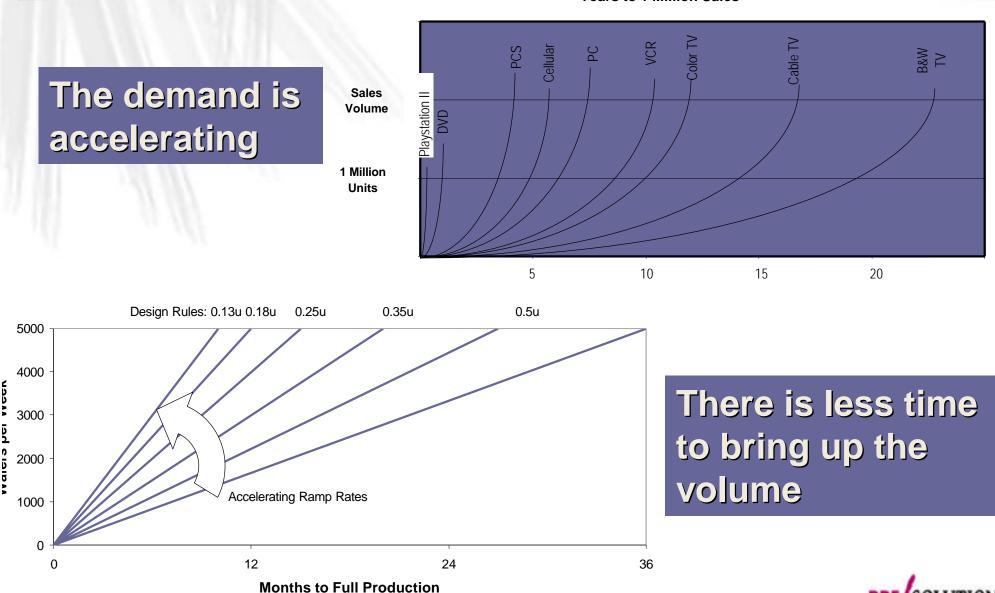
IC Complexity: Processing Steps

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The Window is Tightening

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Years to 1 Million Sales

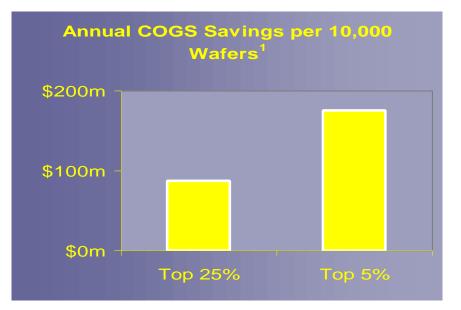
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Missing the Window is Expensive

Three costs:

Lost market share
Increased NRE

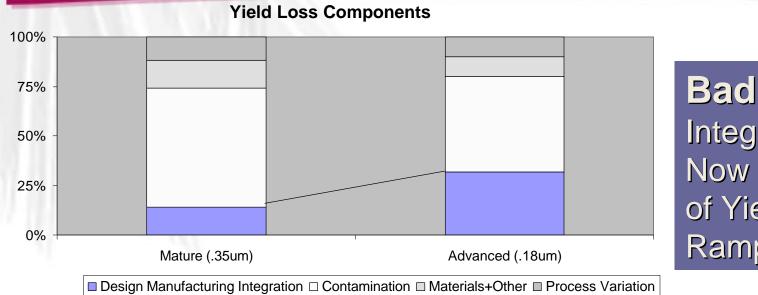
 Increased Costs of Goods Sold (COGS)



Integration effects market entry point, performance, and cost basis



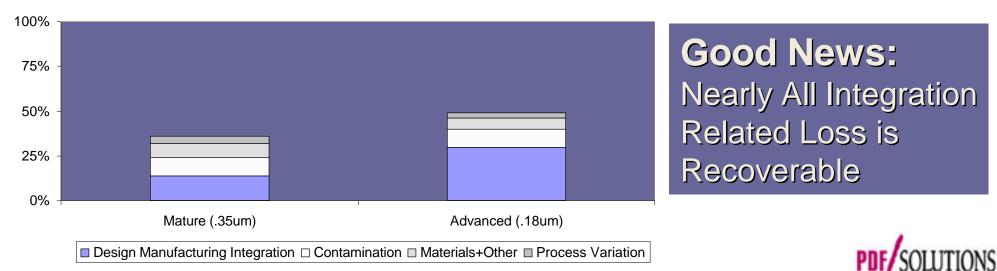
And Those Yield Loss \$\$\$ are Recoverable ...



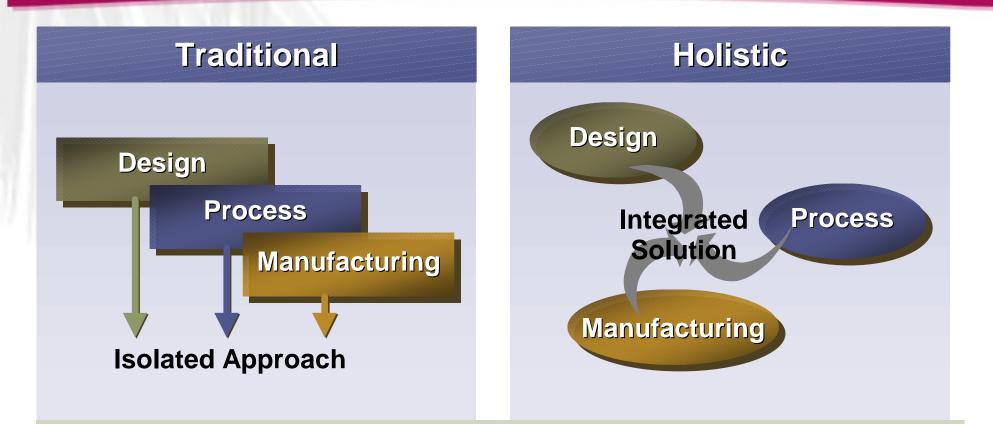
Bad News:

Integration Issues Now Account for 30% of Yield Loss During Ramp





... but, an Integrated Approach is Required



"Ask yourself this: Why does a MIPS core cost 25 cents, and you go to QED and there's a 100-fold increase in value? ... the QED part is worth \$25 because it is implemented in silicon."

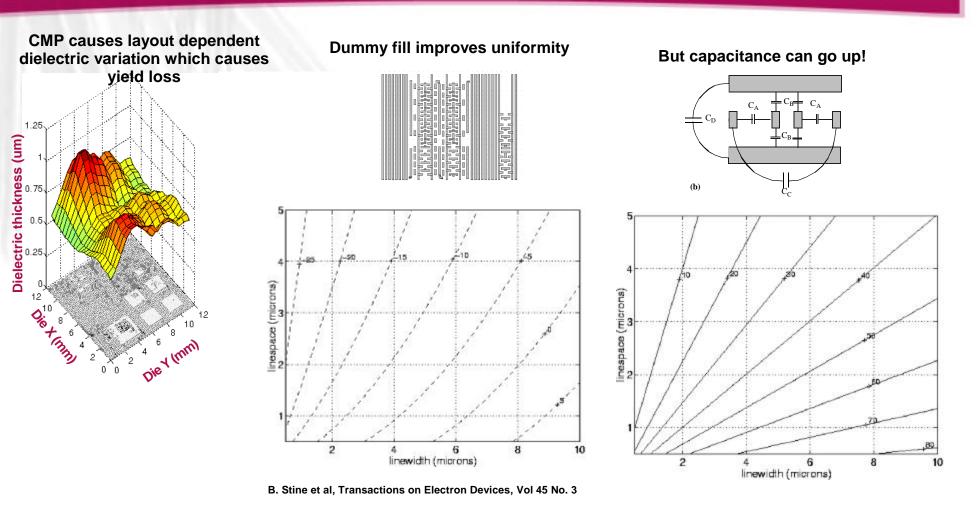
- Rob Chaplinsky, general partner of Mohr Davidow Ventures

Technical Issues Have Both Design and Manufacturing Implications

New Technology	Impact on Design / Manufacturing Interface	Compensation	Design – Manufacturing Issue
Chemical Mechanical Polishing (CMP)	 ILD Variability Depth of focus Capacitance variability 	 Dummy fill Increased design margin 	 What is the circuit performance impact? What is the optimal dummy fill strategy?
I-Line @ 0.35μm DuV @ 0.25μm and below	 Large w/in chip line width variation 	 Optical Proximity Correction 	 Printability verification after OPC? Gap fill issues?
Channel & Source Drain Engineering RTA, Tox, Poly CD	 Increased relative variability of transistor performance 	Statistical designIncrease margins	 Traditional worst case corners not valid
Re-use of large design cores	 Debugging product yield issues 	 Black box yield models 	 Fault localization difficult



Design or Manufacturing Problem? Both!

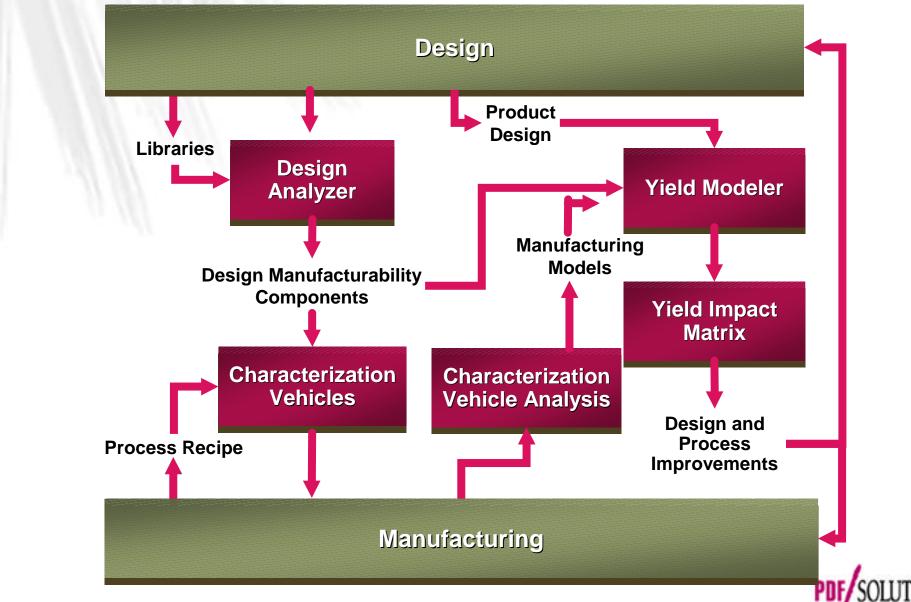


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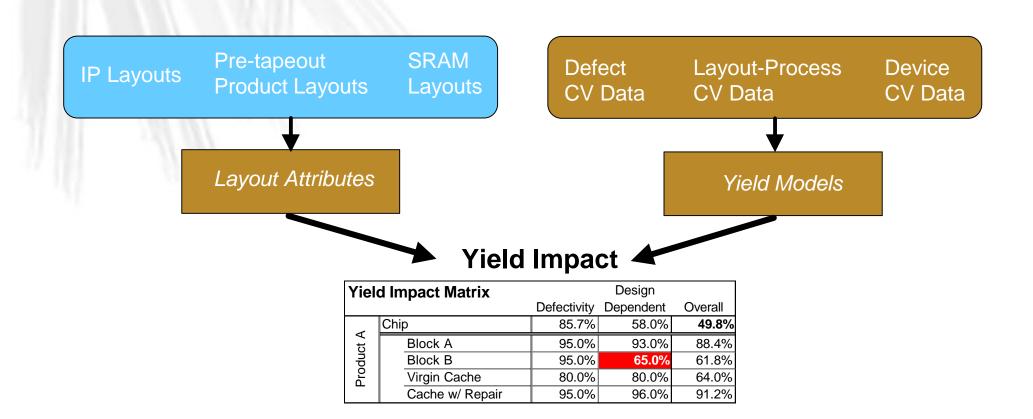
Optimal solution depends on both design and process considerations



Simulating Design - Manufacturing Integration

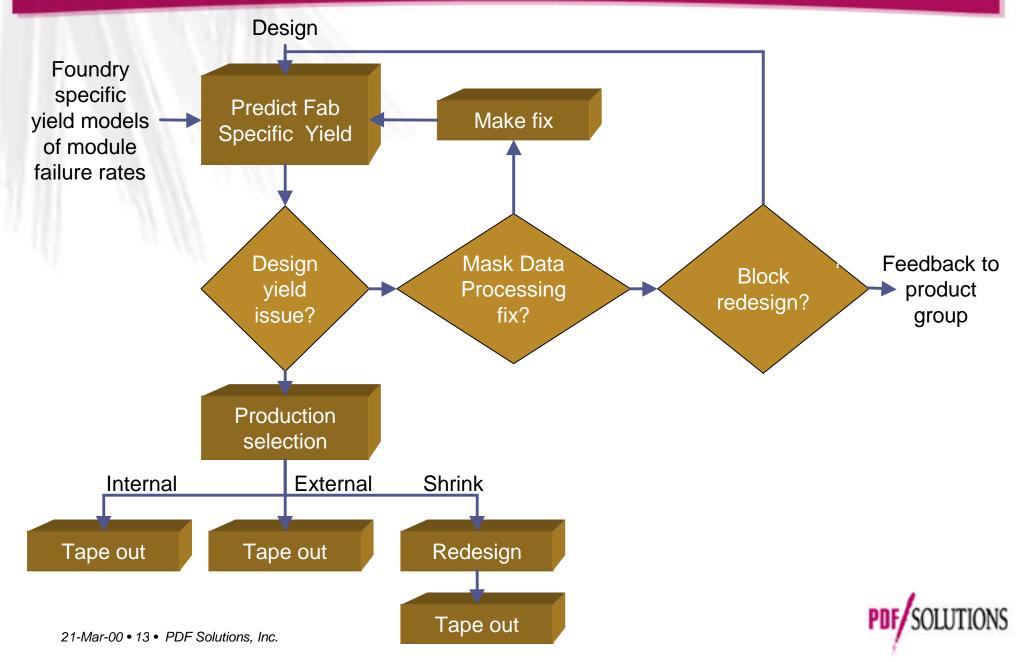


The Yield Impact Matrix





Using Simulated Integration Results to Make Production Decisions



Example 1: Via Short Flow CV Example Floorplan

5	Long Runners				
	Via1 Loading				
Long Rur	Via2 Loading	Con Loa	itact ding	Isolated Vias	Long Ru
Runners	Via2 Misalignment		Contact Misalignment		Runners
	Redundanc		У	Size	

 Via1/Via2/Contact Loading: Compute yield impact of density.

- Via2/Contact Misalignment: Compute yield impact of misalignment of via to underlying layers.
- Redundancy:
 Compare fault rai

Compare fault rates of single via chains to redundant via chains.

• Size:

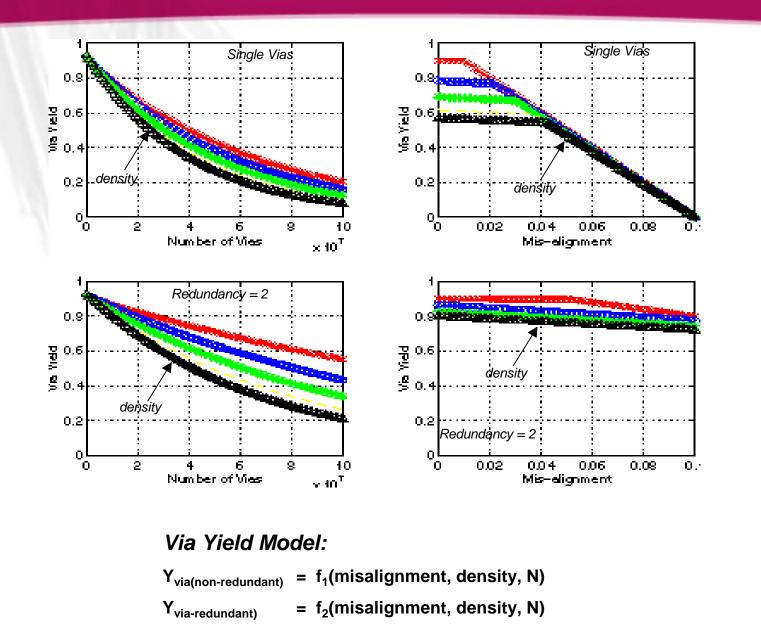
Compute yield impact of via size. Check process margin.

• Long Runners:

Compute yield impact of long metal runs in via chain.

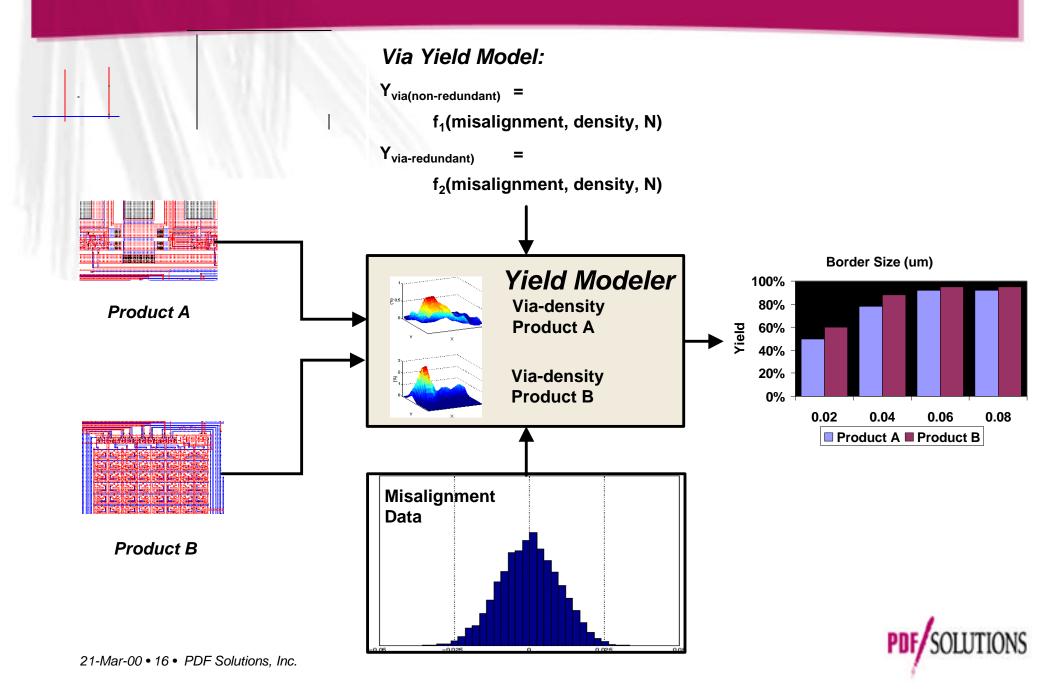


Example 1: Yield Modeling Process Specific Via Yield Model





Example 1: Design Yield Entitlement Product Specific Via Yield Prediction



Example 2: Optimizing Fill For Performance and Yield

Questions about dummy fill algorithm:

- Which layers?
- What pattern?
- Should you exclude sections of the design layout?

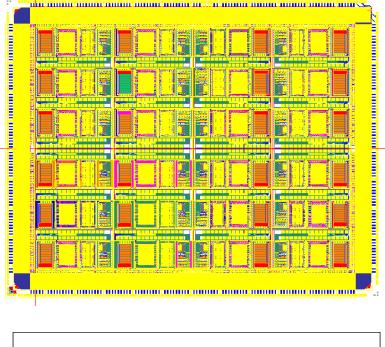
Approach

 Build vehicle to characterize performance/yield dependencies on layout choice

- Build yield models
- Optimize dummy fill for product chips



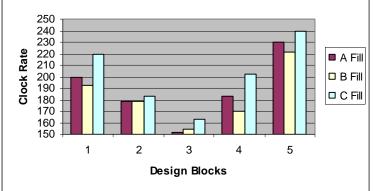
Example 2: Optimizing Fill for Yield and Performance



30 Identical circuits

• Each contains: SRAM, gate dependent and interconnect dominated logic circuits, and analog blocks

 Each variant is a DOE element exploring dummy fill, meta/poly OPC, via sizing options



Some fill patterns have positive impact on yield and performance for some design blocks



Concluding Remarks

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